

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

After forming a stopper film on a semiconductor substrate having a copper wiring layer ~~formed~~ therein, an interlayer insulating film made of a low dielectric constant material is formed on the stopper film. Then, after forming a capping film on the interlayer insulating film, a resist film having a predetermined pattern is formed on the capping film. The capping film and the interlayer insulating film are etched using the resist film as a mask to form an opening reaching the stopper film. After that, ~~a the~~ stopper film exposed ~~at~~ by the opening is etched, with the resist film left in place, to form a via hole. Then, the resist film is removed ~~through~~ by ashing.